

BR2SC2712Q

Rev.A Oct.-2023

/ Descriptions

JF K\$) * E GE Silicon NPN transistor in a SOT-23 Plastic Package.

/ Features

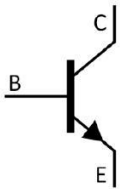
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High voltage, high current, high h_{FE}, low noise, excellent h_{FE} linearity, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

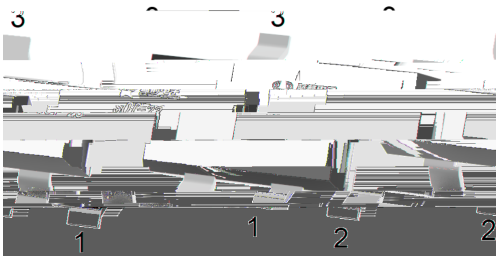
/ Applications

Audio frequency general purpose amplifier applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	O	Y	GR	BL
h _{FE} Range	70 140	120 240	200 400	350 700
Marking	QLO	QLY	QLG	QLL

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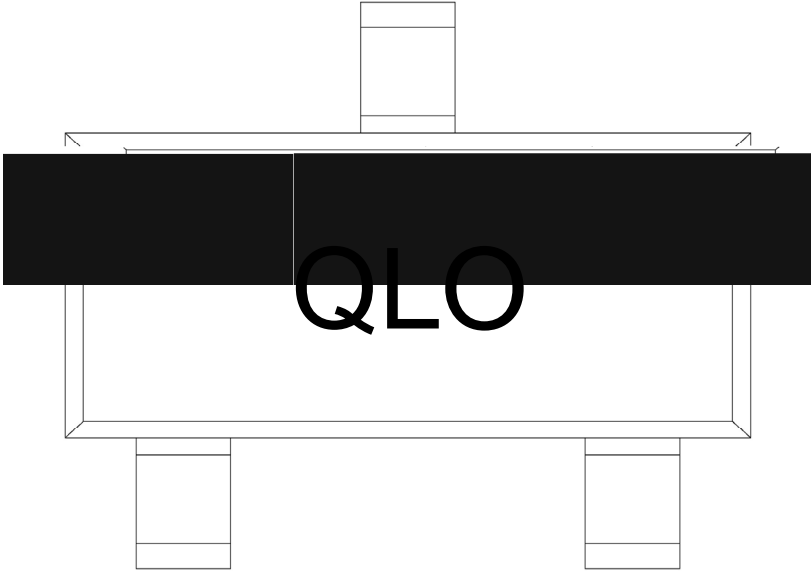


DATA SHEET

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CB0}	60	V
Collector to Emitter Voltage	V_{CE0}	50	V
Emitter to Base Voltage	V_{EB0}	5.0	V
Collector Current	I_C	150	mA
Base Current	I_B	30	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=5.0V$ $I_C=0$			0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=2.0mA$	70		700	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=100mA$ $I_B=10mA$		0.1	0.25	V

/ Marking Instructions



H

C

F

hFE

Note:

H1

C Product Type Code

F hFE Classifications Symbol

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Note:

- 1 150 200 60 120sec; 1.Preheating:150~200 , Time:60~120sec.
- 2 255..5 5..0.5sec; 2.Peak Temp.:255..5 , Duration:5..0.5sec.
- 3 2 10 /sec. 3.Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260..5 10..1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units				Dimension	(unit mm ³)
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box		